Silicon Carbide (SiC) MOSFET - EliteSiC, 23 mohm, 650 V, M3S, TO-247-4L

NTH4L023N065M3S

Features

- Typical $R_{DS(on)}$ = 23 mΩ @ V_{GS} = 18 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 69 nC)
- High Speed Switching with Low Capacitance (C_{oss} = 153 pF)
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with Exemption 7a, Pb−Free 2LI (on second level interconnection)

Applications

- SMPS, Solar Inverters, UPS, Energy Storages, EV Charging Infrastructure

MAXIMUM RATINGS °

Parameter	Symbol	Value	Unit
– –			

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
– –	θ		°
– –	θ		

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value	Unit
– –		– –	

ELECTRICAL CHARACTERISTICS °

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
– –		°				

ELECTRICAL CHARACTERISTICS °

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
–		–	–		–	
–		Ω °	–		–	
			–		–	
			–		–	
–			–		–	μ
–			–		–	
			–		–	
SOURCE TO DRAIN DIODE CHARACTERISTICS						
		– °	–			
		– °	–		–	
		–	–		–	
		μ	–		–	
		°				

TYPICAL CHARACTERISTICS

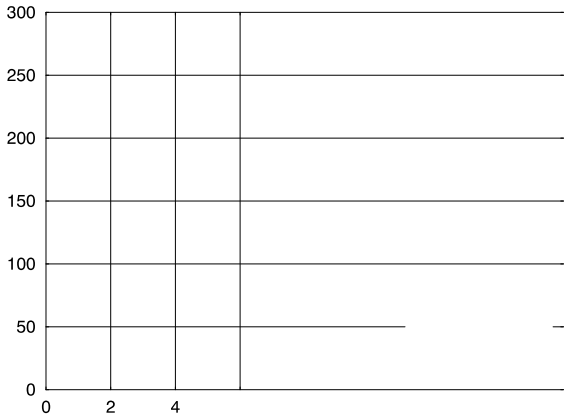

Figure 1. Output Characteristics

Figure 2. Output Characteristics

TYPICAL CHARACTERISTICS

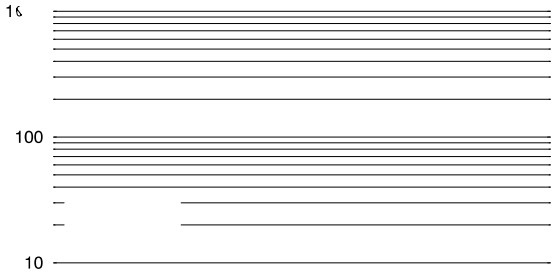

Figure 7. Capacitance Characteristics

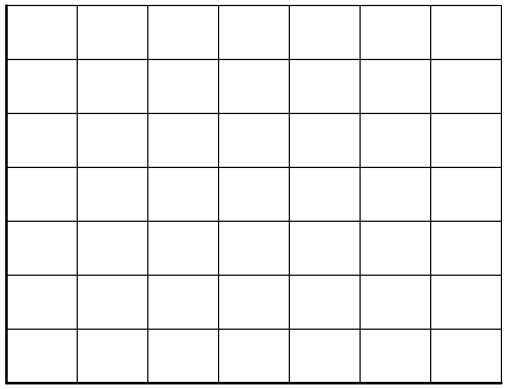

Figure 8. Stored Energy vs Drain to Source Voltage

TO−247−4LD
CASE 340CJ
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